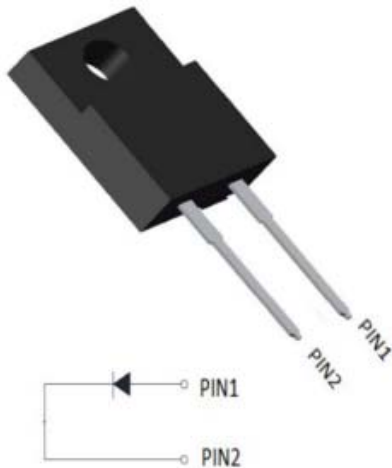


## Silicon Carbide Schottky Diode

$V_{RRM}$	650V
$I_F$ (110°C)	10A
$Q_C$	30nC

### Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI



### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical Data

**Package:** ITO-220AC

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

**Terminals:** Tin plated leads

**Polarity:** As marked

### Maximum Ratings ( $T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106510FQG2
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	$V_{RRM}$	V	650
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	$V_{RSM}$	V	650
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	$V_{DC}$	V	650
Continuous forward current @ $T_c=25^\circ\text{C}$	$I_F$	A	16
Continuous forward current @ $T_c=110^\circ\text{C}$			10
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$ , $t_p=10\text{ms}$ , Half Sine Wave	$I_{FSM}$	A	80
Power Dissipation @ $T_c=25^\circ\text{C}$	$P_{TOT}$	W	43
Power Dissipation @ $T_c=110^\circ\text{C}$			19
$i^2t$ Value @ $T_c=25^\circ\text{C}$ , $t_p=10\text{ms}$	$i^2t$	$\text{A}^2\text{S}$	32
Operating junction and Storage temperature range	$T_j, T_{stg}$	$^\circ\text{C}$	-55 to +175



## Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	$V_F$	V	$I_F=10A, T_J=25^{\circ}C$	1.35	1.55
			$I_F=10A, T_J=175^{\circ}C$	1.8	-
Reverse leakage current	$I_R$	$\mu A$	$V_R=650V, T_J=25^{\circ}C$	0.5	25
			$V_R=650V, T_J=175^{\circ}C$	2	-
Total capacitive charge	$Q_C$	nC	$V_R=400V, T_J=25^{\circ}C, Q_C=\int_0^{V_R} I_C(V)dV$	30	-
Total capacitance	C	$\mu F$	$V_R=0V, f=1MHz$	543	-
			$V_R=200V, f=1MHz$	55	-
			$V_R=400V, f=1MHz$	52	-
Capacitance Stored Energy	$E_C$	$\mu J$	$V_R=400V$	3.7	-

## Thermal Characteristics ( $T_a=25^{\circ}C$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	$R_{J-C}$	$^{\circ}C/W$	3.5

## Typical Characteristics

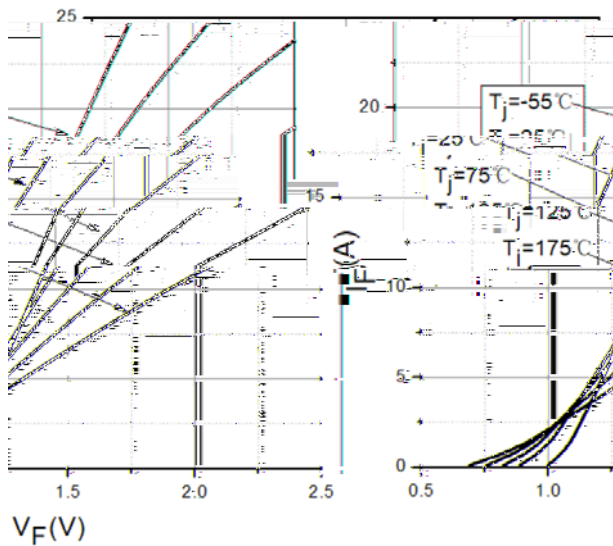


Figure 1. Forward Characteristics

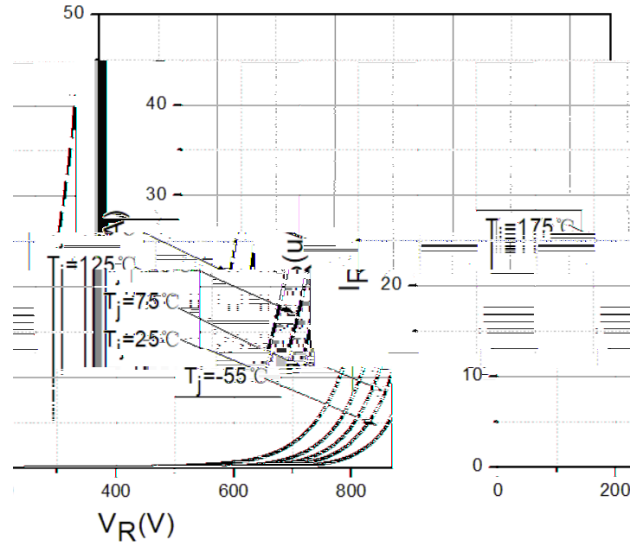


Figure2. Reverse Characteristic

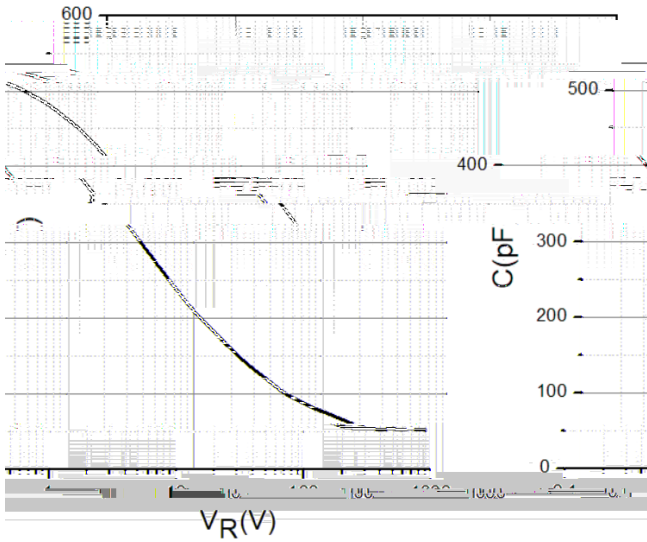


Figure 3. Capacitance vs. Reverse Voltage

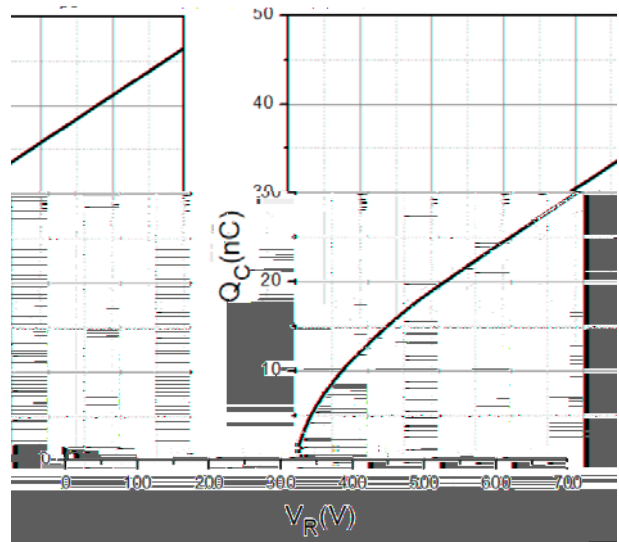


Figure 4. Total Capacitance Charge vs. Reverse Voltage

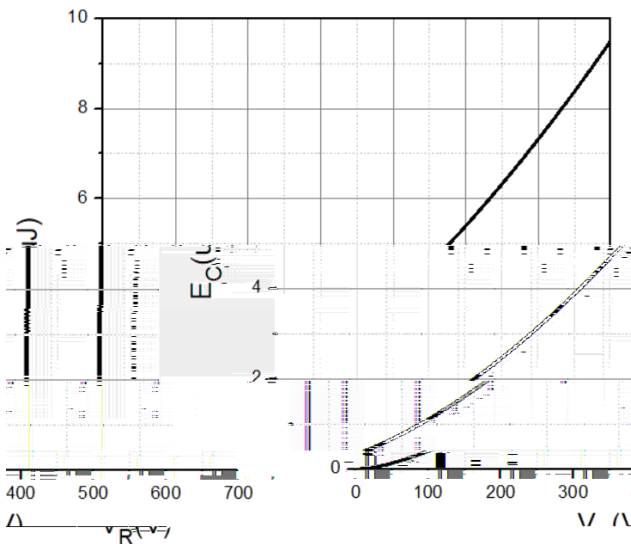


Figure 5. Capacitance Stored Energy

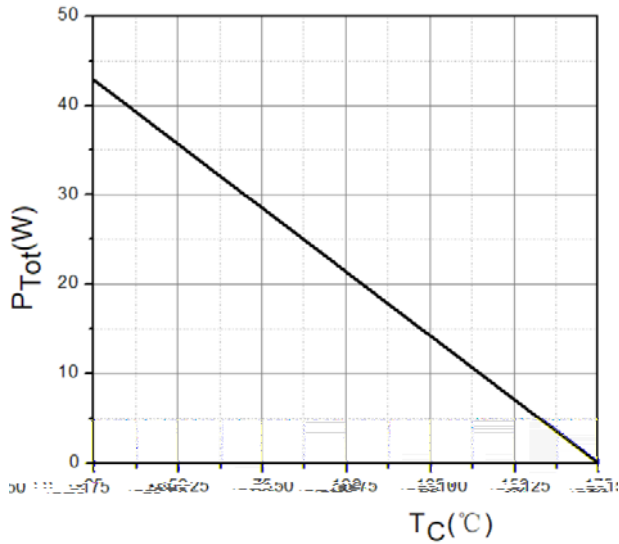


Figure 6. Power Derating

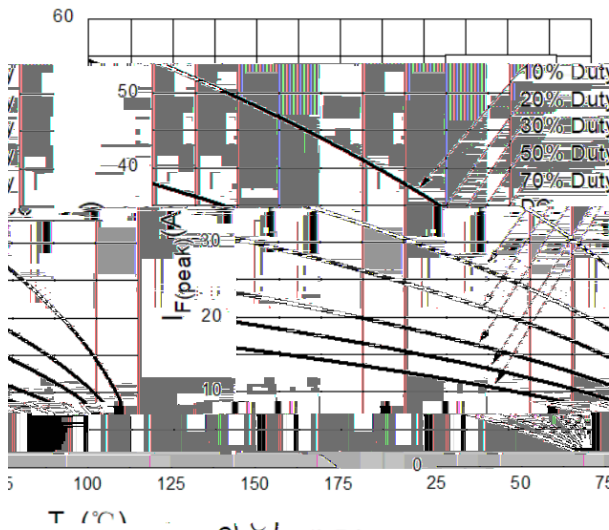


Figure 7. Current Derating

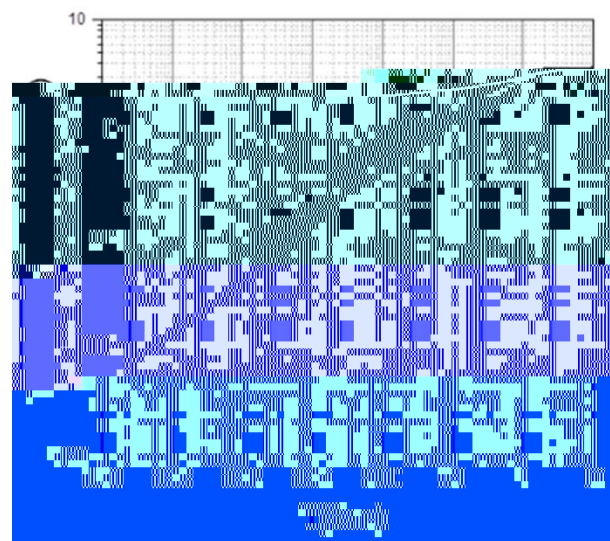
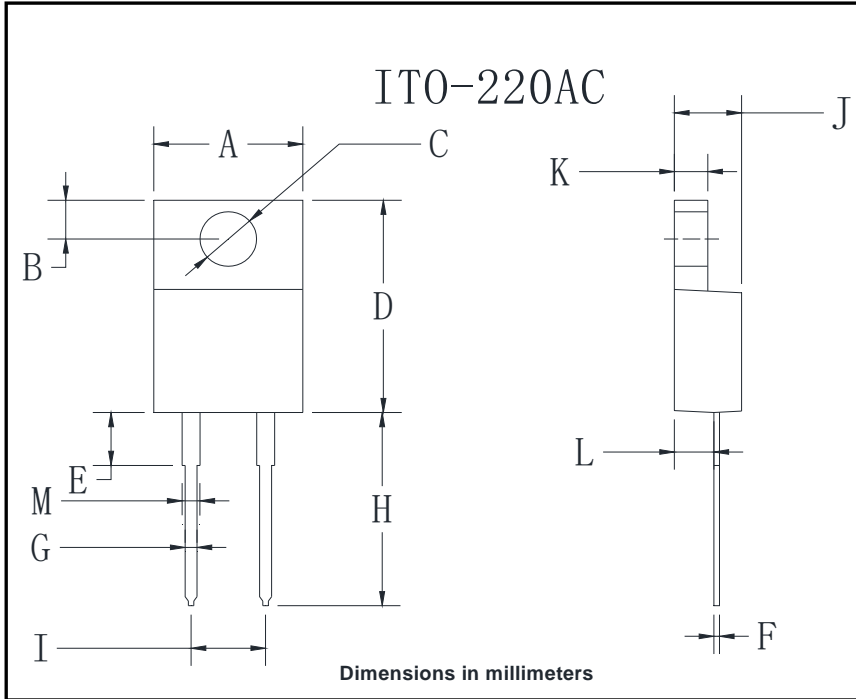


Figure 8. Transient Thermal Impedance



Outline Dimensions



ITO-220AC		
Dim	Min	Max
A	9.8	10.2
B	2.25	2.75
C	2.95	3.45
D	14.75	15.25
E	3.5	4.1
F	0.45	0.75
G	0.45	0.75
H	13.35	14.15
I	4.97	5.23
J	4.3	4.8
K	2.5	2.74
L	2.58	2.82
M	1.03	1.43



## YJD106510FQG2

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### Disclaimer

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